



型号: B5819W

肖特基二极管 SCHOTTKY DIODE

### 主要特性/Features

正向导通电压低 Forward on voltage low

环保护结构提供瞬态保护 The ring protection structure provides transient

极小的恢复时间 minimal recovery time

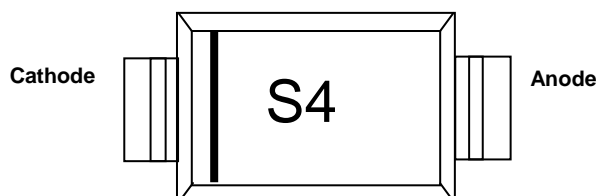
极小的反向电容 Very small reverse capacitance

### 应用/Application

高速开关电路 High speed switch circuit

### 印字/MARKING

### 等效电路/Equivalent Circuit





极限参数/Absolute maximum ratings(Ta=25°C)

Parameter	Symbol	Value	Unit
Peak Repetitive Peak Reverse Voltage Working Peak DC Blocking Voltage	VRRM VRWM VR	40	V
RMS Reverse Voltage	VR(RMS)	28	V
Forward Continuous Current	IFM	350	mA
Repetitive Peak Forward Current(@t≤ 1S)	IFSM	1.5	A
Power Dissipation	Pd	200	mW
Thermal Resistance Junction To Ambient	Rθ JA	300	°C/mW
Storage Temperature	Tstg	-65 ~ 125	°C

电性能参数/Electrical characteristics (Ta=25°C)

参数/Parameter	符号	测试条件	最小值	典型值	最大值	单位
Reverse Breakdown Voltage	V(BR)R	IR=100μ A	40			V
Forward Voltage	VF	IF=20mA			0.37	V
		IF=200mA			0.60	V
Reverse Current	IRM	VR=30V			5.0	μ A
Capacitance Between Terminals	CT	VR=0V, f=1.0MHz			50	pF
Reverse Recovery Time	trr	IF=IR=200mA, Irr=0.1×IR, RL=100Ω		10		nS



### 典型特性曲线图/Typical Characteristics

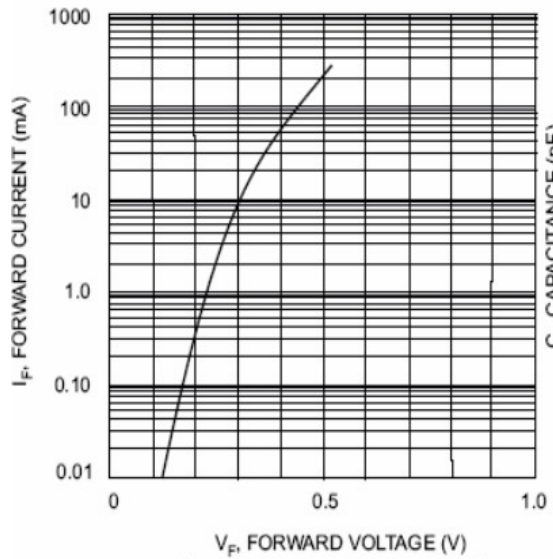


Fig. 1 Typical Forward Characteristics

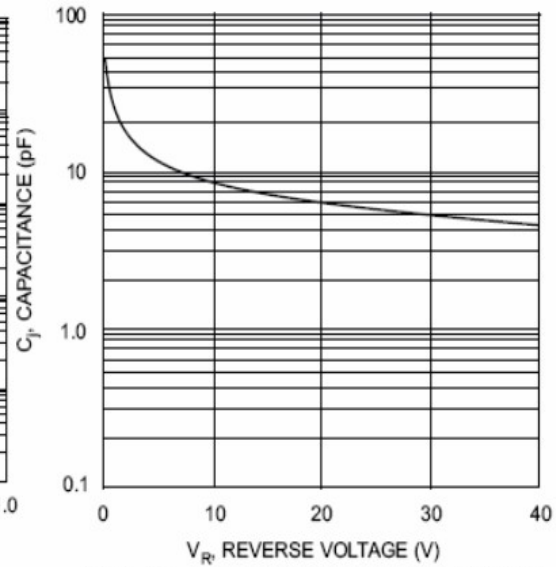
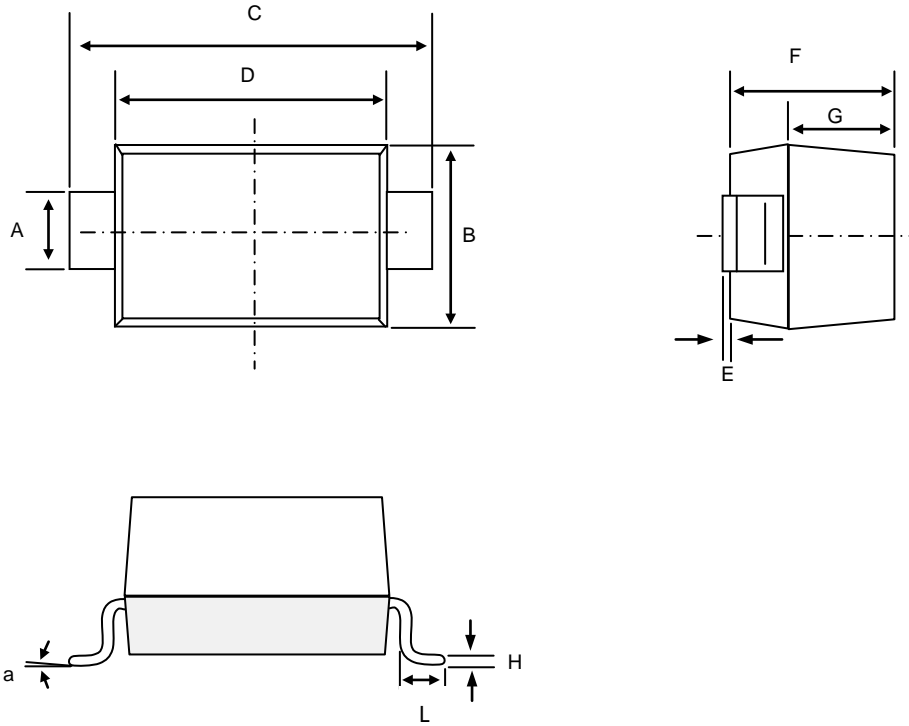


Fig. 2 Typ. Junction Capacitance vs Reverse Voltage



成品外观尺寸/SOD-123 Package Information



Symbol	Dim in mm		
	Min	Nor	Max
A	0.520	0.550	0.570
B	1.400	1.550	1.700
C	3.350	3.650	3.850
D	2.550	2.650	2.850
E	0.000	0.050	0.100
F	1.050	1.100	1.150
G	0.620	0.650	0.670
H	0.100	0.110	0.120
L	0.250	0.350	0.450
a	0°	-	6°